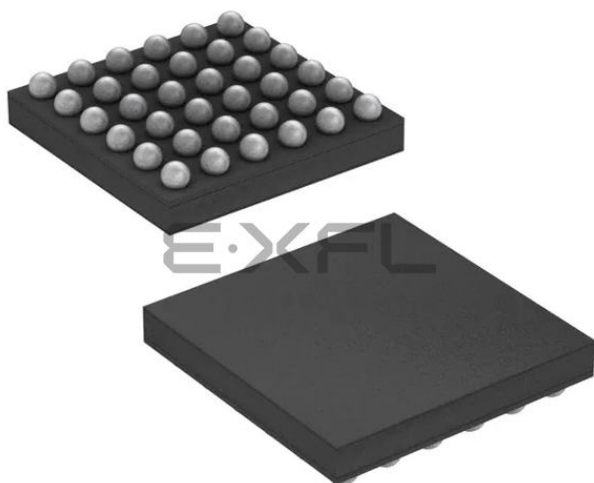




Welcome to [E-XFL.COM](#)

Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	260
Total RAM Bits	-
Number of I/O	23
Number of Gates	10000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-20°C ~ 85°C (TJ)
Package / Case	36-WFBGA, CSPBGA
Supplier Device Package	36-UCSP (3x3)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agln010v2-ucg36

IGLOO nano Products Available in the Z Feature Grade

IGLOO nano-Z Devices	AGLN030Z*	AGLN060Z*	AGLN125Z*	AGLN250Z*
Packages	QN48	–	–	–
	QN68	–	–	–
	UC81	–	–	–
	CS81	CS81	CS81	CS81
	VQ100	VQ100	VQ100	VQ100

Note: *Not recommended for new designs.

Temperature Grade Offerings

	AGLN010	AGLN015*	AGLN020		AGLN060	AGLN125	AGLN250
Package				AGLN030Z*	AGLN060Z*	AGLN125Z*	AGLN250Z*
UC36	C, I	–	–	–	–	–	–
QN48	C, I	–	–	C, I	–	–	–
QN68	–	C, I	C, I	C, I	–	–	–
UC81	–	–	C, I	C, I	–	–	–
CS81	–	–	C, I	C, I	C, I	C, I	C, I
VQ100	–	–	–	C, I	C, I	C, I	C, I

Note: * Not recommended for new designs.

C = Enhanced Commercial temperature range: –20°C to +85°C junction temperature

I = Industrial temperature range: –40°C to +100°C junction temperature

Contact your local Microsemi representative for device availability: <http://www.microsemi.com/soc/contact/default.aspx>.

Table of Contents

IGLOO nano Device Overview

General Description	1-1
---------------------------	-----

IGLOO nano DC and Switching Characteristics

General Specifications	2-1
Calculating Power Dissipation	2-7
User I/O Characteristics	2-15
VersaTile Characteristics	2-57
Global Resource Characteristics	2-63
Clock Conditioning Circuits	2-70
Embedded SRAM and FIFO Characteristics	2-73
Embedded FlashROM Characteristics	2-87
JTAG 1532 Characteristics	2-88

Pin Descriptions

Supply Pins	3-1
User Pins	3-2
JTAG Pins	3-3
Special Function Pins	3-4
Packaging	3-4
Related Documents	3-5

Package Pin Assignments

UC36	4-1
UC81	4-3
CS81	4-6
QN48	4-15
QN68	4-18
VQ100	4-22

Datasheet Information

List of Changes	5-1
Datasheet Categories	5-8
Safety Critical, Life Support, and High-Reliability Applications Policy	5-8

Table 2-10 • Quiescent Supply Current (IDD) Characteristics, IGLOO nano Sleep Mode*

	Core Voltage	AGLN010	AGLN015	AGLN020	AGLN060	AGLN125	AGLN250	Units
VCCI = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	μA
VCCI = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	μA
VCCI = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	μA
VCCI = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	μA
VCCI = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	μA

Note: $*I_{DD} = N_{BANKS} * I_{CCI}$

Table 2-11 • Quiescent Supply Current (IDD) Characteristics, IGLOO nano Shutdown Mode

	Core Voltage	AGLN010	AGLN015	AGLN020	AGLN060	AGLN125	AGLN250	Units
Typical (25°C)	1.2 V / 1.5 V	0	0	0	0	0	0	μA

Table 2-12 • Quiescent Supply Current (IDD), No IGLOO nano Flash*Freeze Mode¹

	Core Voltage	AGLN010	AGLN015	AGLN020	AGLN060	AGLN125	AGLN250	Units
ICCA Current²								
Typical (25°C)	1.2 V	3.7	5	5	10	13	18	μA
	1.5 V	8	14	14	20	28	44	μA
ICCI or JTAG Current								
VCCI / VJTAG = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	μA
VCCI / VJTAG = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	μA
VCCI / VJTAG = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	μA
VCCI / VJTAG = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	μA
VCCI / VJTAG = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	μA

Notes:

1. $IDD = N_{BANKS} * ICCI + ICCA$. JTAG counts as one bank when powered.
2. Includes VCC, VCCPLL, and VPUMP currents.

Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-21 • Summary of Maximum and Minimum DC Input and Output Levels
Applicable to Commercial and Industrial Conditions—Software Default Settings

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength ²	Slew Rate	VIL		VIH		VOL	VOH	IOL ¹	IOH ¹
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTTL / 3.3 V LVCMOS	8 mA	8 mA	High	–0.3	0.8	2	3.6	0.4	2.4	8	8
3.3 V LVCMOS Wide Range ³	100 μ A	8 mA	High	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	100 μ A	100 μ A
2.5 V LVCMOS	8 mA	8 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	8	8
1.8 V LVCMOS	4 mA	4 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4
1.5 V LVCMOS	2 mA	2 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS ⁴	1 mA	1 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	1	1
1.2 V LVCMOS Wide Range ^{4,5}	100 μ A	1 mA	High	–0.3	0.3 * VCCI	0.7 * VCCI	3.6	0.1	VCCI – 0.1	100 μ A	100 μ A

Notes:

1. Currents are measured at 85°C junction temperature.
2. The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is $\pm 100 \mu$ A. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
3. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range, as specified in the JESD8-B specification.
4. Applicable to IGLOO nano V2 devices operating at VCCI $\geq$ VCC.
5. All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range, as specified in the JESD8-12 specification.

Table 2-22 • Summary of Maximum and Minimum DC Input Levels
Applicable to Commercial and Industrial Conditions

DC I/O Standards	Commercial ¹		Industrial ²	
	IIL ³	IIH ⁴	IIL ³	IIH ⁴
	μ A	μ A	μ A	μ A
3.3 V LVTTTL / 3.3 V LVCMOS	10	10	15	15
3.3 V LVCOMS Wide Range	10	10	15	15
2.5 V LVCMOS	10	10	15	15
1.8 V LVCMOS	10	10	15	15
1.5 V LVCMOS	10	10	15	15
1.2 V LVCMOS ⁵	10	10	15	15
1.2 V LVCMOS Wide Range ⁵	10	10	15	15

Notes:

1. Commercial range ($-20^{\circ}\text{C} < T_A < 70^{\circ}\text{C}$)
2. Industrial range ($-40^{\circ}\text{C} < T_A < 85^{\circ}\text{C}$)
3. I_{IH} is the input leakage current per I/O pin over recommended operating conditions, where $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
4. I_{IL} is the input leakage current per I/O pin over recommended operating conditions, where $-0.3 \text{ V} < V_{IN} < V_{IL}$.
5. Applicable to IGLOO nano V2 devices operating at VCCI $\geq$ VCC.

Summary of I/O Timing Characteristics – Default I/O Software Settings

Table 2-23 • Summary of AC Measuring Points

Standard	Measuring Trip Point (Vtrip)
3.3 V LVTTTL / 3.3 V LVCMOS	1.4 V
3.3 V LVCMOS Wide Range	1.4 V
2.5 V LVCMOS	1.2 V
1.8 V LVCMOS	0.90 V
1.5 V LVCMOS	0.75 V
1.2 V LVCMOS	0.60 V
1.2 V LVCMOS Wide Range	0.60 V

Table 2-24 • I/O AC Parameter Definitions

Parameter	Parameter Definition
t_{DP}	Data to Pad delay through the Output Buffer
t_{PY}	Pad to Data delay through the Input Buffer
t_{DOUT}	Data to Output Buffer delay through the I/O interface
t_{EOUT}	Enable to Output Buffer Tristate Control delay through the I/O interface
t_{DIN}	Input Buffer to Data delay through the I/O interface
t_{HZ}	Enable to Pad delay through the Output Buffer—HIGH to Z
t_{ZH}	Enable to Pad delay through the Output Buffer—Z to HIGH
t_{LZ}	Enable to Pad delay through the Output Buffer—LOW to Z
t_{ZL}	Enable to Pad delay through the Output Buffer—Z to LOW
t_{ZHS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to HIGH
t_{ZLS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to LOW

Detailed I/O DC Characteristics

Table 2-27 • Input Capacitance

Symbol	Definition	Conditions	Min.	Max.	Units
C_{IN}	Input capacitance	$V_{IN} = 0, f = 1.0 \text{ MHz}$		8	pF
C_{INCLK}	Input capacitance on the clock pin	$V_{IN} = 0, f = 1.0 \text{ MHz}$		8	pF

Table 2-28 • I/O Output Buffer Maximum Resistances ¹

Standard	Drive Strength	$R_{PULL-DOWN}$ (Ω) ²	$R_{PULL-UP}$ (Ω) ³
3.3 V LVTTTL / 3.3V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
3.3 V LVCMOS Wide Range	100 μ A	Same as equivalent software default drive	
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
1.5 V LVCMOS	2 mA	200	224
1.2 V LVCMOS ⁴	1 mA	315	315
1.2 V LVCMOS Wide Range ⁴	100 μ A	315	315

Notes:

1. These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on V_{CCI} , drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models posted at <http://www.microsemi.com/soc/download/ibis/default.aspx>.
2. $R_{(PULL-DOWN-MAX)} = (V_{OLspec}) / I_{OLspec}$
3. $R_{(PULL-UP-MAX)} = (V_{CCImax} - V_{OHspec}) / I_{OHspec}$
4. Applicable to IGLOO nano V2 devices operating at $V_{CCI} \geq V_{CC}$.

3.3 V LVCMOS Wide Range

Table 2-40 • Minimum and Maximum DC Input and Output Levels for LVCMOS 3.3 V Wide Range

3.3 V LVCMOS Wide Range ¹	Equivalent Software Default Drive Strength Option ⁴	VIL		VIH		VOL	VOH	IOL	I _{OH}	IIL ²	IIH ³
Drive Strength		Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	μA	μA	μA ⁵	μA ⁵
100 μA	2 mA	−0.3	0.8	2	3.6	0.2	VCCI − 0.2	100	100	10	10
100 μA	4 mA	−0.3	0.8	2	3.6	0.2	VCCI − 0.2	100	100	10	10
100 μA	6 mA	−0.3	0.8	2	3.6	0.2	VCCI − 0.2	100	100	10	10
100 μA	8 mA	−0.3	0.8	2	3.6	0.2	VCCI − 0.2	100	100	10	10

Notes:

1. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V Wide Range, as specified in the JEDEC JESD8-B specification.
2. I_{IL} is the input leakage current per I/O pin over recommended operating conditions where $-0.3 < V_{IN} < V_{IL}$.
3. I_{IH} is the input leakage current per I/O pin over recommended operating conditions where $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
4. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100 \mu A$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
5. Currents are measured at 85°C junction temperature.
6. Software default selection is highlighted in gray.

Fully Registered I/O Buffers with Asynchronous Clear

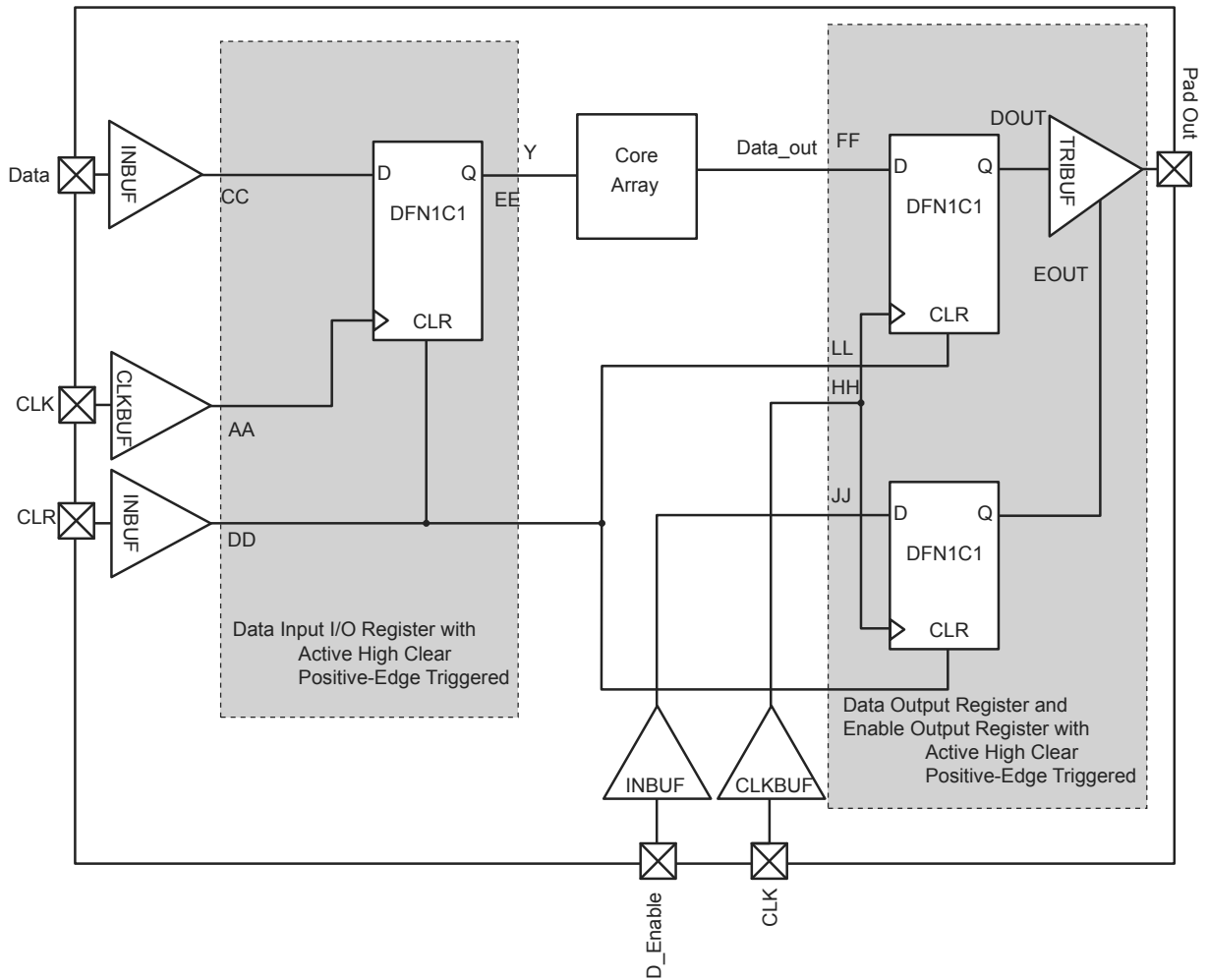


Figure 2-13 • Timing Model of the Registered I/O Buffers with Asynchronous Clear

Table 2-71 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

Note: *See Figure 2-13 on page 2-43 for more information.

1.2 V DC Core Voltage

Table 2-75 • Output Data Register Propagation Delays
Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$

Parameter	Description	Std.	Units
t_{OCLKQ}	Clock-to-Q of the Output Data Register	1.52	ns
t_{OSUD}	Data Setup Time for the Output Data Register	1.15	ns
t_{OHD}	Data Hold Time for the Output Data Register	0.00	ns
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	1.96	ns
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	1.96	ns
t_{OREMCLR}	Asynchronous Clear Removal Time for the Output Data Register	0.00	ns
t_{ORECCLR}	Asynchronous Clear Recovery Time for the Output Data Register	0.24	ns
t_{OREMPRE}	Asynchronous Preset Removal Time for the Output Data Register	0.00	ns
t_{ORECPRE}	Asynchronous Preset Recovery Time for the Output Data Register	0.24	ns
t_{OWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Data Register	0.19	ns
t_{OWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Data Register	0.19	ns
t_{OCKMPWH}	Clock Minimum Pulse Width HIGH for the Output Data Register	0.31	ns
t_{OCKMPWL}	Clock Minimum Pulse Width LOW for the Output Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

VersaTile Characteristics

VersaTile Specifications as a Combinatorial Module

The IGLOO nano library offers all combinations of LUT-3 combinatorial functions. In this section, timing characteristics are presented for a sample of the library. For more details, refer to the *IGLOO, ProASIC3, SmartFusion and Fusion Macro Library Guide for Software v10.1*.

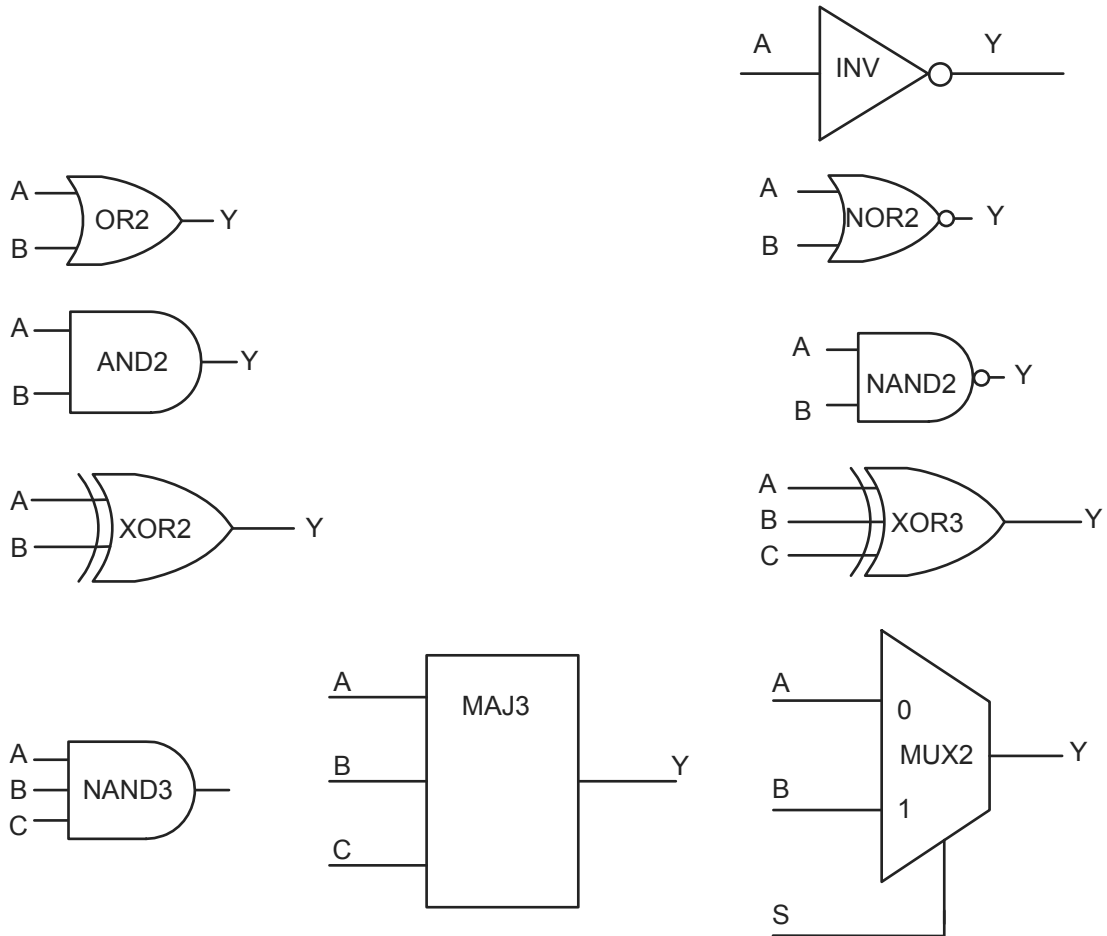


Figure 2-21 • Sample of Combinatorial Cells

VersaTile Specifications as a Sequential Module

The IGLOO nano library offers a wide variety of sequential cells, including flip-flops and latches. Each has a data input and optional enable, clear, or preset. In this section, timing characteristics are presented for a representative sample from the library. For more details, refer to the *IGLOO, ProASIC3, SmartFusion and Fusion Macro Library Guide for Software v10.1*.

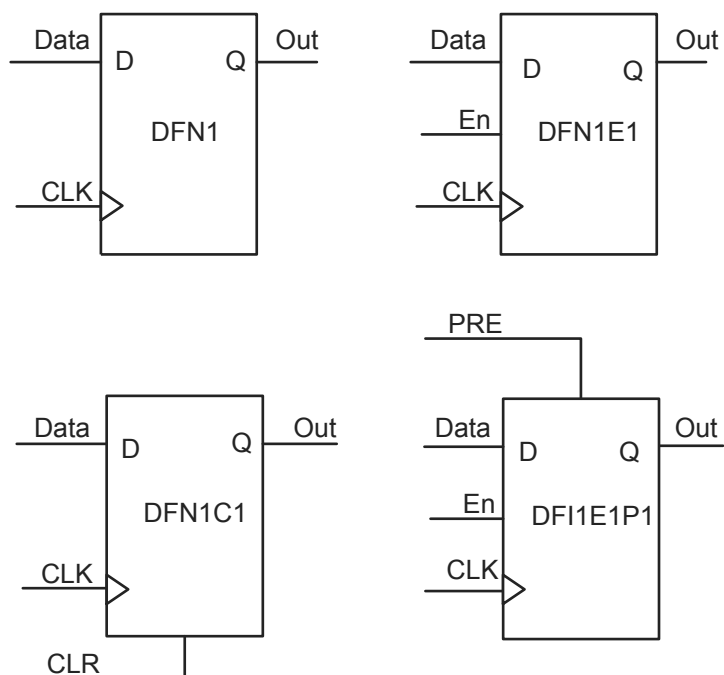


Figure 2-23 • Sample of Sequential Cells

1.2 V DC Core Voltage

Table 2-87 • Register Delays
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$

Parameter	Description	Std.	Units
t_{CLKQ}	Clock-to-Q of the Core Register	1.61	ns
t_{SUD}	Data Setup Time for the Core Register	1.17	ns
t_{HD}	Data Hold Time for the Core Register	0.00	ns
t_{SUE}	Enable Setup Time for the Core Register	1.29	ns
t_{HE}	Enable Hold Time for the Core Register	0.00	ns
t_{CLR2Q}	Asynchronous Clear-to-Q of the Core Register	0.87	ns
t_{PRE2Q}	Asynchronous Preset-to-Q of the Core Register	0.89	ns
t_{REMCLR}	Asynchronous Clear Removal Time for the Core Register	0.00	ns
t_{RECCLR}	Asynchronous Clear Recovery Time for the Core Register	0.24	ns
t_{REMPRE}	Asynchronous Preset Removal Time for the Core Register	0.00	ns
t_{RECPRE}	Asynchronous Preset Recovery Time for the Core Register	0.24	ns
t_{WCLR}	Asynchronous Clear Minimum Pulse Width for the Core Register	0.46	ns
t_{WPRE}	Asynchronous Preset Minimum Pulse Width for the Core Register	0.46	ns
t_{CKMPWH}	Clock Minimum Pulse Width HIGH for the Core Register	0.95	ns
t_{CKMPWL}	Clock Minimum Pulse Width LOW for the Core Register	0.95	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-92 • AGLN125 Global Resource
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.		Units
		Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	1.36	1.71	ns
t_{RCKH}	Input High Delay for Global Clock	1.39	1.82	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.43	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-93 • AGLN250 Global Resource
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.		Units
		Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	1.39	1.73	ns
t_{RCKH}	Input High Delay for Global Clock	1.41	1.84	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.43	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Timing Waveforms

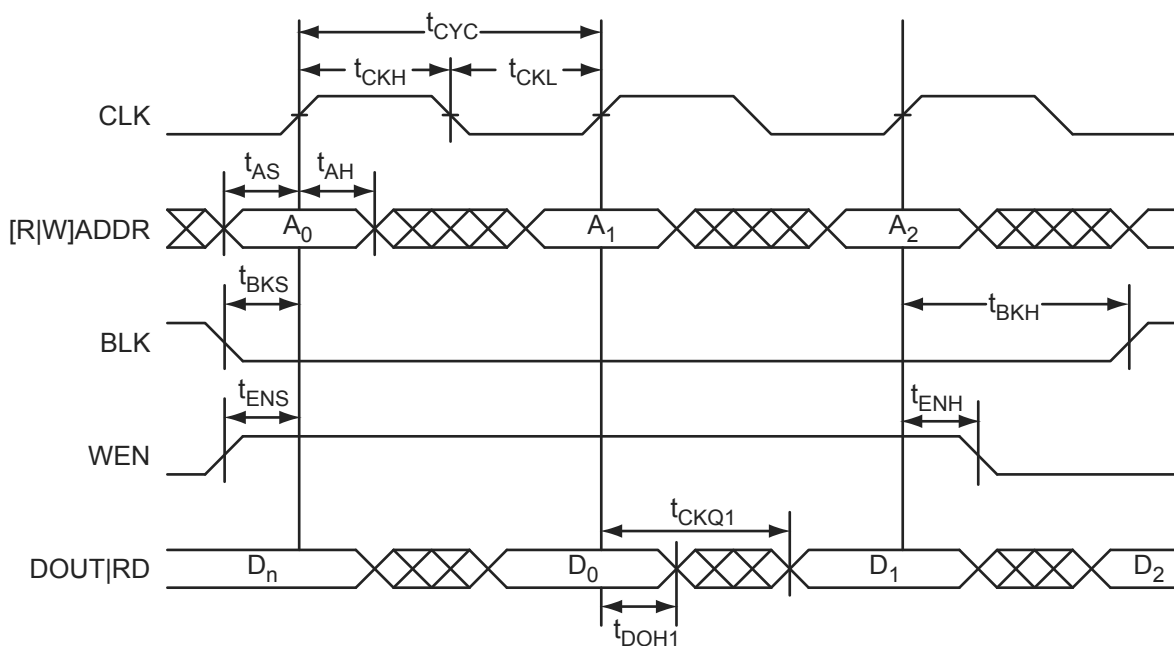


Figure 2-28 • RAM Read for Pass-Through Output. Applicable to Both RAM4K9 and RAM512x18.

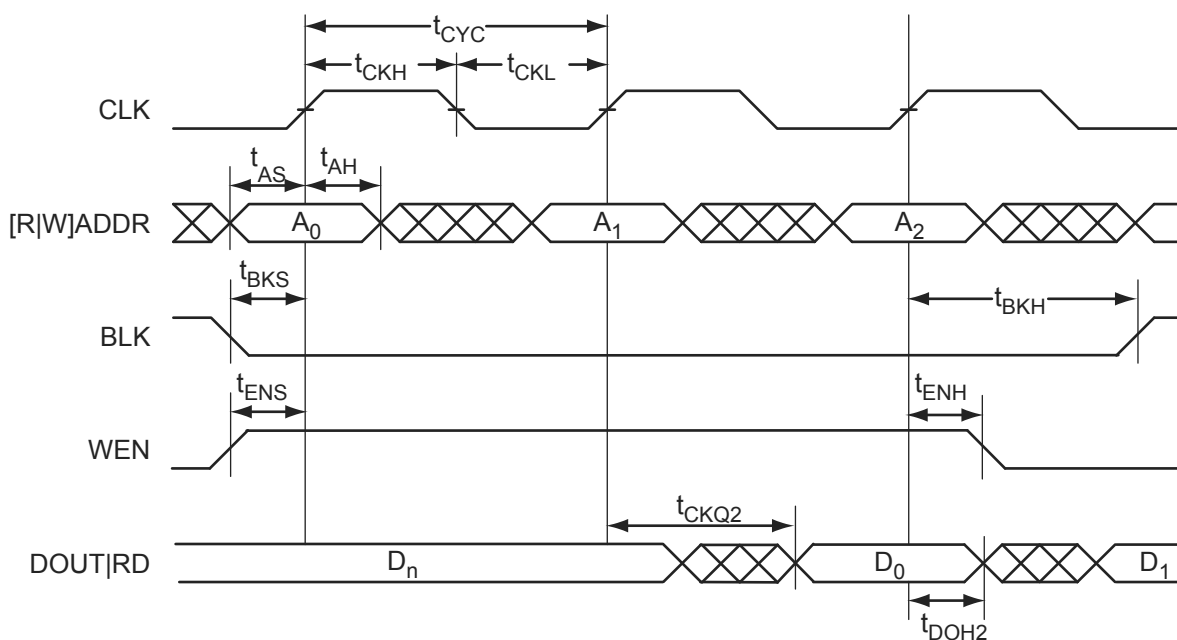


Figure 2-29 • RAM Read for Pipelined Output. Applicable to Both RAM4K9 and RAM512x18.

FIFO

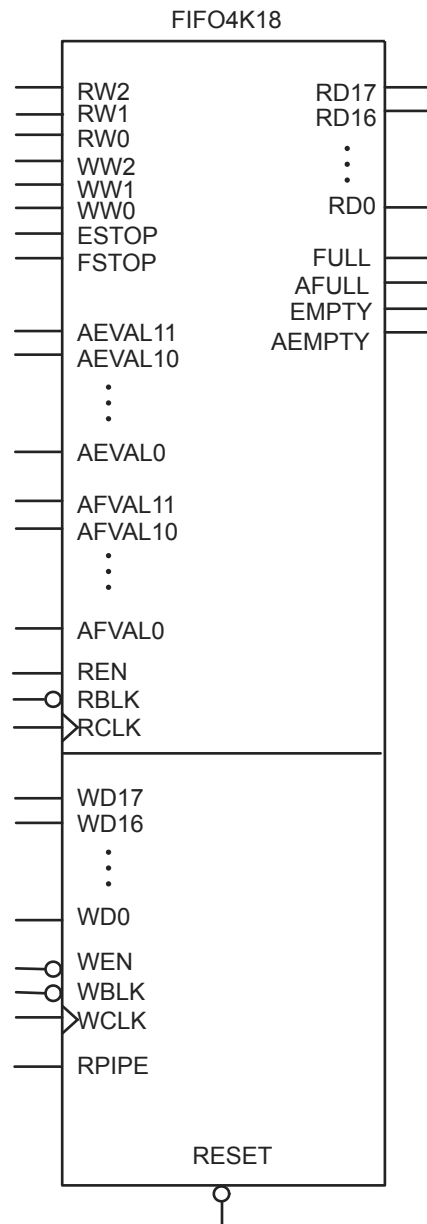
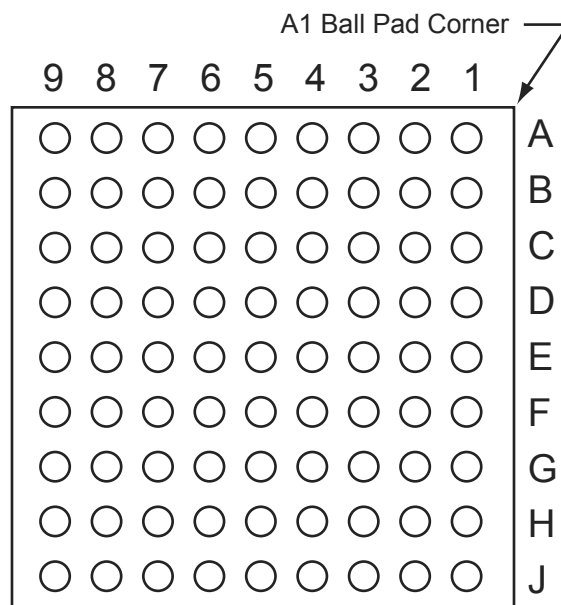


Figure 2-33 • FIFO Model

CS81



Note: This is the bottom view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/soc/products/solutions/package/docs.aspx>.

QN68	
Pin Number	AGLN015 Function
1	IO60RSB2
2	IO54RSB2
3	IO52RSB2
4	IO50RSB2
5	IO49RSB2
6	GEC0/IO48RSB2
7	GEA0/IO47RSB2
8	VCC
9	GND
10	VCCIB2
11	IO46RSB2
12	IO45RSB2
13	IO44RSB2
14	IO43RSB2
15	IO42RSB2
16	IO41RSB2
17	IO40RSB2
18	FF/IO39RSB1
19	IO37RSB1
20	IO35RSB1
21	IO33RSB1
22	IO31RSB1
23	IO30RSB1
24	VCC
25	GND
26	VCCIB1
27	IO27RSB1
28	IO25RSB1
29	IO23RSB1
30	IO21RSB1
31	IO19RSB1
32	TCK
33	TDI
34	TMS
35	VPUMP

QN68	
Pin Number	AGLN015 Function
36	TDO
37	TRST
38	VJTAG
39	IO17RSB0
40	IO16RSB0
41	GDA0/IO15RSB0
42	GDC0/IO14RSB0
43	IO13RSB0
44	VCCIB0
45	GND
46	VCC
47	IO12RSB0
48	IO11RSB0
49	IO09RSB0
50	IO05RSB0
51	IO00RSB0
52	IO07RSB0
53	IO03RSB0
54	IO18RSB1
55	IO20RSB1
56	IO22RSB1
57	IO24RSB1
58	IO28RSB1
59	NC
60	GND
61	NC
62	IO32RSB1
63	IO34RSB1
64	IO36RSB1
65	IO61RSB2
66	IO58RSB2
67	IO56RSB2
68	IO63RSB2

VQ100	
Pin Number	AGLN030Z Function
1	GND
2	IO82RSB1
3	IO81RSB1
4	IO80RSB1
5	IO79RSB1
6	IO78RSB1
7	IO77RSB1
8	IO76RSB1
9	GND
10	IO75RSB1
11	IO74RSB1
12	GEC0/IO73RSB1
13	GEA0/IO72RSB1
14	GEB0/IO71RSB1
15	IO70RSB1
16	IO69RSB1
17	VCC
18	VCCIB1
19	IO68RSB1
20	IO67RSB1
21	IO66RSB1
22	IO65RSB1
23	IO64RSB1
24	IO63RSB1
25	IO62RSB1
26	IO61RSB1
27	FF/IO60RSB1
28	IO59RSB1
29	IO58RSB1
30	IO57RSB1
31	IO56RSB1
32	IO55RSB1
33	IO54RSB1
34	IO53RSB1
35	IO52RSB1

VQ100	
Pin Number	AGLN030Z Function
36	IO51RSB1
37	VCC
38	GND
39	VCCIB1
40	IO49RSB1
41	IO47RSB1
42	IO46RSB1
43	IO45RSB1
44	IO44RSB1
45	IO43RSB1
46	IO42RSB1
47	TCK
48	TDI
49	TMS
50	NC
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	IO41RSB0
58	IO40RSB0
59	IO39RSB0
60	IO38RSB0
61	IO37RSB0
62	IO36RSB0
63	GDB0/IO34RSB0
64	GDA0/IO33RSB0
65	GDC0/IO32RSB0
66	VCCIB0
67	GND
68	VCC
69	IO31RSB0
70	IO30RSB0

VQ100	
Pin Number	AGLN030Z Function
71	IO29RSB0
72	IO28RSB0
73	IO27RSB0
74	IO26RSB0
75	IO25RSB0
76	IO24RSB0
77	IO23RSB0
78	IO22RSB0
79	IO21RSB0
80	IO20RSB0
81	IO19RSB0
82	IO18RSB0
83	IO17RSB0
84	IO16RSB0
85	IO15RSB0
86	IO14RSB0
87	VCCIB0
88	GND
89	VCC
90	IO12RSB0
91	IO10RSB0
92	IO08RSB0
93	IO07RSB0
94	IO06RSB0
95	IO05RSB0
96	IO04RSB0
97	IO03RSB0
98	IO02RSB0
99	IO01RSB0
100	IO00RSB0

VQ100		VQ100		VQ100	
Pin Number	AGLN060Z Function	Pin Number	AGLN060Z Function	Pin Number	AGLN060Z Function
1	GND	35	IO62RSB1	69	IO31RSB0
2	GAA2/IO51RSB1	36	IO61RSB1	70	GBC2/IO29RSB0
3	IO52RSB1	37	VCC	71	GBB2/IO27RSB0
4	GAB2/IO53RSB1	38	GND	72	IO26RSB0
5	IO95RSB1	39	VCCIB1	73	GBA2/IO25RSB0
6	GAC2/IO94RSB1	40	IO60RSB1	74	VMV0
7	IO93RSB1	41	IO59RSB1	75	GNDQ
8	IO92RSB1	42	IO58RSB1	76	GBA1/IO24RSB0
9	GND	43	IO57RSB1	77	GBA0/IO23RSB0
10	GFB1/IO87RSB1	44	GDC2/IO56RSB1	78	GBB1/IO22RSB0
11	GFB0/IO86RSB1	45*	GDB2/IO55RSB1	79	GBB0/IO21RSB0
12	VCOMPLF	46	GDA2/IO54RSB1	80	GBC1/IO20RSB0
13	GFA0/IO85RSB1	47	TCK	81	GBC0/IO19RSB0
14	VCCPLF	48	TDI	82	IO18RSB0
15	GFA1/IO84RSB1	49	TMS	83	IO17RSB0
16	GFA2/IO83RSB1	50	VMV1	84	IO15RSB0
17	VCC	51	GND	85	IO13RSB0
18	VCCIB1	52	VPUMP	86	IO11RSB0
19	GEC1/IO77RSB1	53	NC	87	VCCIB0
20	GEB1/IO75RSB1	54	TDO	88	GND
21	GEB0/IO74RSB1	55	TRST	89	VCC
22	GEA1/IO73RSB1	56	VJTAG	90	IO10RSB0
23	GEA0/IO72RSB1	57	GDA1/IO49RSB0	91	IO09RSB0
24	VMV1	58	GDC0/IO46RSB0	92	IO08RSB0
25	GNDQ	59	GDC1/IO45RSB0	93	GAC1/IO07RSB0
26	GEA2/IO71RSB1	60	GCC2/IO43RSB0	94	GAC0/IO06RSB0
27	FF/GEB2/IO70RSB1	61	GCB2/IO42RSB0	95	GAB1/IO05RSB0
28	GEC2/IO69RSB1	62	GCA0/IO40RSB0	96	GAB0/IO04RSB0
29	IO68RSB1	63	GCA1/IO39RSB0	97	GAA1/IO03RSB0
30	IO67RSB1	64	GCC0/IO36RSB0	98	GAA0/IO02RSB0
31	IO66RSB1	65	GCC1/IO35RSB0	99	IO01RSB0
32	IO65RSB1	66	VCCIB0	100	IO00RSB0
33	IO64RSB1	67	GND		
34	IO63RSB1	68	VCC		

Note: *The bus hold attribute (hold previous I/O state in Flash*Freeze mode) is not supported for pin 45 in AGLN060Z-VQ100.